VS-ST1230C...K Series

Vishay Semiconductors

Phase Control Thyristors (Hockey PUK Version), 1745 A



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K-PUK (A-24)

PRIMARY CHARACTERISTICS						
I _{T(AV)}	1745 A					
V _{DRM} /V _{RRM}	800 V, 1200 V, 1400 V, 1600 V					
V _{TM}	1.62 V					
I _{GT}	100 mA					
TJ	-40 °C to +125 °C					
Package	K-PUK (A-24)					
Circuit configuration	Single SCR					

FEATURES

- · Center amplifying gate
- · Metal case with ceramic insulator
- International standard case K-PUK (A-24)
- High profile hockey PUK
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- DC motor controls
- · Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
1		1745	А				
I _{T(AV)}	T _{hs}	55	°C				
1		3200	A				
I _{T(RMS)}	T _{hs}	25	°C				
1	50 Hz	33 500	٨				
I _{TSM}	60 Hz	35 100	A				
l ² t	50 Hz	5615	kA ² s				
1-1	60 Hz	5126	KA-S				
V _{DRM} /V _{RRM}		800 to 1600	V				
t _q	Typical	200	μs				
TJ		-40 to +125	°C				

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA				
	08	800	900					
VS-ST1230CK	12	1200	1300	100				
14		1400	1400 1500					
	16	1600	1700					

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ABSOLUTE MAXIMUM RATING	5						
PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS	
Maximum average on-state current		180° condu	180° conduction, half sine wave		1745 (700)	А	
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (85)	°C	
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink temp	erature double side cooled	3200		
		t = 10 ms	No voltage		33 500		
Maximum peak, one-cycle		t = 8.3 ms	reapplied		35 100	А	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{BBM}		28 200	kA ² s	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	29 500		
		t = 10 ms	No voltage	initial T _J = T _J maximum	5615		
Marine 124 for frain a	l ² t	t = 8.3 ms	reapplied		5126		
Maximum I ² t for fusing	141	t = 10 ms	100 % V _{BBM}		3971		
		t = 8.3 ms	reapplied		3625	1	
Maximum I²√t for fusing	l²√t	t = 0.1 to 10) ms, no voltage	reapplied	56 150	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.93	v	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$), $T_J = T_J$ maxin	num	1.02	v	
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum				
High level value of on-state slope resistance	r _{t2}	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			0.16	mΩ	
Maximum on-state voltage	V _{TM}	$I_{pk} = 4000 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.62	V	
Maximum holding current	Ι _Η	T _ 05 °C	anada aunahi 1	2. V registive lead	600	m۸	
Typical latching current	١L	$1_{\rm J} = 25^{-1}{\rm C},$	anoue supply 1	2 V resistive load	1000	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,t_r \le 1~\mu s$ T_J = T_J maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/µs V_d = 0.67 % V_{DRM} , T_J = 25 °C	1.9	110
Typical turn-off time	tq	I_{TM} = 550 A, T_J = T_J maximum, dl/dt = 40 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	200	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA





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TRIGGERING							
PARAMETER	SYMBOL	т	ST CONDITIONS	VALUES		UNITS	
FARAMETER	STMBOL	16	STCONDITIONS	typ.	Max.	UNITS	
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 ms$	1	6	W	
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	:	3	vv	
Maximum peak positive gate current	I _{GM}			3	.0	А	
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms			V	
Maximum peak negative gate voltage	- V _{GM}						
		T _J = -40 °C		200	-		
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger/	100	200	mA	
		T _J = 125 °C	current/voltage are the lowest	50	-		
		T _J = -40 °C	value which will trigger all units	1.4	-		
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	12 V anode to cathode applied	1.1	3.0	V	
		T _J = 125 °C		0.9	-		
DC gate current not to trigger	I _{GD}		Maximum gate current/	1	0	mA	
DC gate voltage not to trigger	V _{GD}	T _J = T _J maximum	voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	°C		
Maximum storage temperature range	T _{Stg}		-40 to 150			
Maximum thermal resistance,	р	DC operation single side cooled	0.042			
junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.021	κ/w		
Maximum thermal resistance,	D	DC operation single side cooled	0.006	r\/ vv		
case to heatsink	R _{thC-hs}	DC operation double side cooled	0.003			
Mounting force, ± 10 %			24 500 (2500)	N (kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet	K-PUK (A-	-24)		

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		-	NGULAR JCTION	TEST CONDITIONS	UNITS			
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE					
180°	0.003	0.003	0.002	0.002					
120°	0.004	0.004	0.004	0.004					
90°	0.005	0.005	0.005	0.005	$T_J = T_J maximum$	K/W			
60°	0.007	0.007	0.007	0.007					
30°	0.012	0.012	0.012	0.012					

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



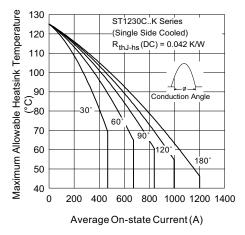


Fig. 1 - Current Ratings Characteristics

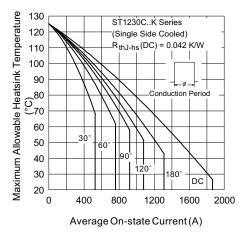


Fig. 2 - Current Ratings Characteristics

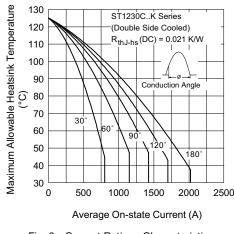


Fig. 3 - Current Ratings Characteristics

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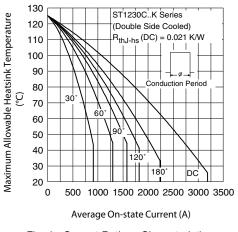


Fig. 4 - Current Ratings Characteristics

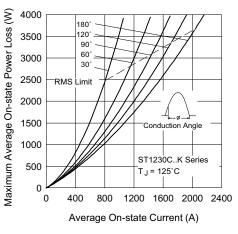


Fig. 5 - On-State Power Loss Characteristics

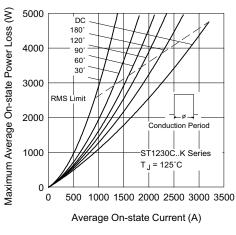


Fig. 6 - On-State Power Loss Characteristics

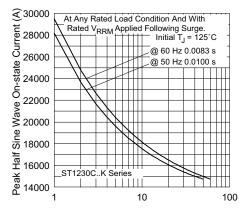
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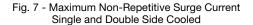
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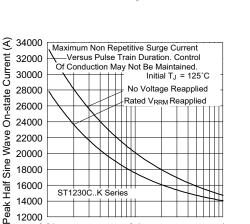
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Number Of Equal Amplitude Half Cycle Current Pulses (N)





0.1 Pulse Train Duration (s)

Fig. 8 - Maximum Non-Repetitive Surge Current

Single and Double Side Cooled

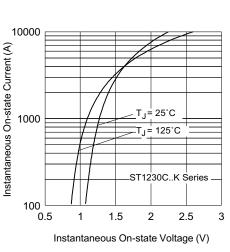
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16000

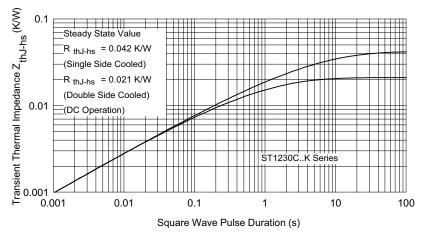
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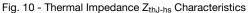
12000

0.01









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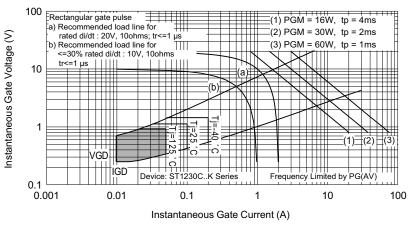


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

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Device code	VS-	ST	123	0	с	16	к	1	-	
	1	2	3	4	5	6	7	8	9	I
	1 - 2 - 3 -	Thy	ristor	niconduo art num!		oduct				
	4 - 5 -		convert cerami	er grade c PUK	e					
	6 - 7 -			de x 100 ise K-Pl			oltage F	Ratings	table)	
	8 -	1 =	fast-on		ls (gate	and aux	ciliary ca	athode	unsolde	ed leads) ered leads) leads)
	9 -			dt:• Nor	ne = 500		standar	d select		d leads)

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			

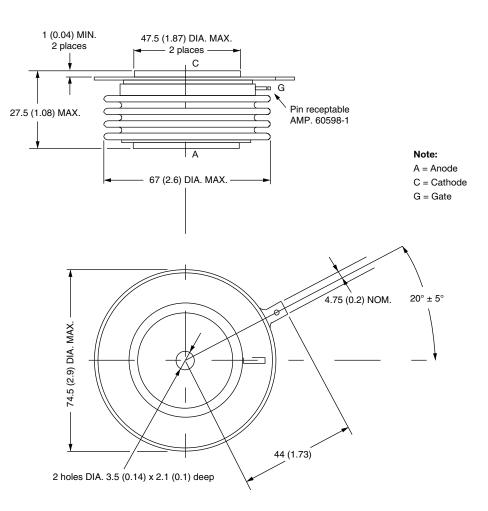


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K-PUK (A-24)

DIMENSIONS in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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